

## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the above-referenced application.

### **Listing of Claims:**

Claims 1 – 19 (Cancelled)

20. (Currently amended) A semiconductor device, comprising:

a semiconductor substrate;

an organic film having low dielectric constant and including no silicon, said organic film being formed on said semiconductor substrate; and

[[a]] at least two silicon included organic films formed on a lower surface, an upper surface, or both lower and upper surfaces of said organic film having low dielectric constant, wherein a first silicon included organic film is formed on said lower surface and a second silicon included organic film is formed on said upper surface.

21. (Currently amended) A semiconductor device as claimed in claim 20, wherein a conductive film is selectively buried into an opening portion of stacked films consisting of said silicon included organic films formed on a lower surface, an upper surface, or both said lower and upper surfaces of said organic film having low dielectric constant.

22. (Original) A semiconductor device as claimed in claim 20, wherein said silicon included organic film is formed by a polymer of divinyl-siloxane-benzocyclobutene.

23. (Currently amended) A semiconductor device, comprising:

[[a]] at least two silicon included organic films composed of a first organic compound including silicon; and

a silicon non-included organic film which is composed of a second organic compound including substantially no silicon and which is ~~connected with~~ disposed between said silicon included organic films.

24. (Currently amended) A semiconductor device, comprising:

a substrate;

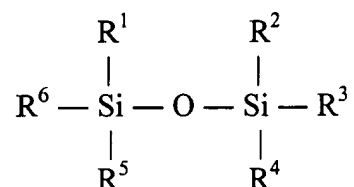
a first silicon included organic film which is formed on an upper side of said substrate and which is composed of a first organic compound including silicon;

a silicon non-included organic film which is formed on an upper side of said first silicon included organic film and which is composed of a second organic compound including substantially no silicon and in which a wiring trench is formed down to said first silicon included organic film; [[and]]

a second silicon included organic film which is formed on an upper side of said silicon non-included organic film; and

a conductor formed within said wiring trench.

25. (Currently amended) A semiconductor device as claimed in claim 23, wherein said first organic compound includes a polymer of a compound having the following structural formula;



wherein R<sup>1</sup> through R<sup>6</sup> [[:]] are hydrocarbon radicals.

26. (Original) A semiconductor device as claimed in claim 23, wherein said first organic compound includes a polymer of divinyl-siloxane-benzocyclobutene.

27. (Original) A semiconductor device as claimed in claim 23, wherein said first organic compound includes a polymer of siloxane-polyimide.

28. (Currently amended) A semiconductor device, comprising:

[[A]] a hard mask, characterized in that wherein said hard mask is for use in etching an organic film composed of an organic compound including no silicon, said ~~organic film~~ hard mask including a silicon-included organic film composed of an first organic compound including silicon; and

an etching stopper film, wherein said etching stopper film is for use in etching said organic film composed of the organic compound including no silicon, said etching stopper film including a second organic compound including silicon.

29. (Cancelled)